



Figure 1. SEM images of nanoscale patterns with different geometries and feature sizes fabricated with electron beam lithography: (a) radial lines with gap size up to 1000 nm with the distance between two neighboring lines changing by 10 nm within 1 μm ; math defined lines with (b) different curvatures and (c, d) different intersection angles. (d) SEM image taken at 30° tilt after the ALE process: 200 nm deep etching, 850 cycles. The scale bars are 30 μm (a, b, c) and 500 nm (d).